

EAST Search History (23 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	55	landing adj pad near20 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:04
L2	380	planarization near4 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:04
L3	262	planari?ation near4 (silicon adj nitride) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:05
L4	153	planari?ation near4 (silicon adj nitride) and transistor and @ad<"20030411"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:06
L5	9	planari?ation near4 (silicon adj nitride) and transistor and @ad<"20030411" and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:08
L6	9	planari?ation near4 (silicon adj nitride) and transistor and @ad<"20030411" and contact adj plug and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:13
L7	11	planari?ation near4 (silicon adj nitride) and @ad<"20030411" and contact adj plug and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:17
L8	2	("5166771").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 17:21
L9	12	reflow\$3 near10 silicon adj nitride near10 (planari?ation planari?ed planari?ing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:22

EAST Search History

L10	15	reflow\$3 near10 (silicon adj nitride) near10 (planari?ation planari?ed planari?ing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:43
L11	7	reflow\$3 near10 (silicon adj nitride) near10 (planari?ation planari?ed planari?ing) and silicon adj nitride near6 (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 17:55
L12	8	conformal near2 (silicon adj nitride) near6 (thick thickness) near6 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 18:22
L13	9931	((257/208) or (257/211) or (257/296) or (257/300) or (257/301) or (257/304) or (257/311) or (257/532) or (257/906) or (257/908)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 18:23
L14	7	13 and (landing adj pad liner) and (passivati\$2 near1 (film layer)) and contact adj plug and (FET MOSFET MOS MISFET transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 18:25
L15	2	((hui-min near2 mao).in. (yi-nan near1 chen).in. nanya.as.) and (landing adj pad liner).clm. and (passivati\$2 near1 (film layer)).clm. and contact adj plug.clm. and (FET MOSFET MOS MISFET transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 18:28
L16	1	((hui-min near2 mao).in. (yi-nan near1 chen).in. nanya.as.) and (landing adj pad liner).clm. and (passivati\$2 near1 (film layer)).clm. and contact adj plug.clm. and (FET MOSFET MOS MISFET transistor) and (poly-Si polysilicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 18:28
S1	5	"733984".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/10 14:01
S2	106	contact adj hole near6 bit adj line. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 07:19

EAST Search History

S3	55	contact adj hole near6 bit adj line. clm. and contact adj hole.ab,ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 07:20
S4	2	contact adj hole near6 bit adj line. clm. and contact adj hole.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 07:25
S5	32	bit adj line near2 contact adj hole.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:30
S6	243	contact adj (plug hole) and (bit adj line bitline) and transistor and gate adj stack and "257"/\$9.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 16:49
S7	29	(US-20050026329-\$ or US-20040262671-\$ or US-20040262657-\$ or US-20040206994-\$ or US-20040198007-\$ or US-20040108535-\$ or US-20040036177-\$ or US-20040000717-\$ or US-20030027395-\$ or US-20020135072-\$ or US-20020125508-\$ or US-20020119624-\$ or US-20020098654-\$).did. or (US-6885542-\$ or US-6838737-\$ or US-6806187-\$ or US-6787839-\$ or US-6740923-\$ or US-6682984-\$ or US-6576944-\$ or US-6531350-\$ or US-6459116-\$ or US-6365453-\$ or US-6348709-\$ or US-6333240-\$ or US-6333225-\$ or US-6329263-\$ or US-6043119-\$ or US-5679970-\$). did.	US-PGPUB; USPAT	OR	OFF	2005/07/09 16:44
S8	4365	((257/296) or (257/301) or (257/304) or (257/311) or (257/208) or (257/211)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/09 16:50
S9	50	S8 and (short-circuit short) near4 (contact adj (hole plug))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:49

EAST Search History

S10	0	contact adj hole near6 polysicon near3 (liner conformal\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:50
S11	0	contact adj hole near6 polysicon near6 (liner conformal\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:50
S12	0	contact adj (plug hole) near6 polysicon near6 (liner conformal\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:50
S13	39	(storage adj node contact adj (plug hole)) near6 polysilicon near6 (liner conformal\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:50
S14	39	(storage adj node contact adj (plug hole)) near6 polysilicon near6 (liner conformal\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:51
S15	34	(US-20050026329-\$ or US-20040262671-\$ or US-20040262657-\$ or US-20040206994-\$ or US-20040198007-\$ or US-20040108535-\$ or US-20040036177-\$ or US-20040000717-\$ or US-20030027395-\$ or US-20020135072-\$ or US-20020125508-\$ or US-20020119624-\$ or US-20020098654-\$ or US-20050012128-\$ or US-20040201043-\$ or US-20050095857-\$).did. or (US-6885542-\$ or US-6838737-\$ or US-6806187-\$ or US-6787839-\$ or US-6740923-\$ or US-6682984-\$ or US-6576944-\$ or US-6531350-\$ or US-6459116-\$ or US-6365453-\$ or US-6348709-\$ or US-6333240-\$ or US-6333225-\$ or US-6329263-\$ or US-6043119-\$ or US-5679970-\$ or US-6274426-\$ or US-6225214-\$). did.	US-PGPUB; USPAT	OR	OFF	2005/07/09 19:48

EAST Search History

S16	2495	(257/296).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/09 19:48
S17	1592	S16 and ("poly-Si" polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 19:49
S18	942	S16 and ("poly-Si" polysilicon) and (contact adj hole contact adj plug plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 20:03
S19	1505	polysilicon near1 spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 20:03
S20	50	polysilicon near1 spacer and contact adj plug and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 20:08
S21	50	polysilicon near1 spacer and contact adj plug and gate and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 20:53
S22	19	polysilicon near2 spacer and contact adj plug and gate and polysilicon and second adj2 spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 20:59
S23	8	polysilicon adj spacer and contact adj plug and gate and polysilicon and second adj2 spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:08
S24	9	polysilicon adj spacer and polysilicon and second adj2 spacer and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:12
S25	115	(polysilicon poly-Si silicon) near1 spacer and second adj2 spacer and contact adj (hole plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:13

EAST Search History

S26	51	(polysilicon poly-Si silicon) adj spacer and second adj2 spacer and contact adj (hole plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:13
S27	11	(polysilicon poly-Si silicon) adj spacer and second adj2 spacer and contact adj (hole plug) and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:23
S28	0	(polysilicon poly-Si silicon) adj liner and second adj2 spacer and contact adj (hole plug) and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:23
S29	1	(polysilicon poly-Si silicon) adj liner and contact adj (hole plug) and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:24
S30	1	(polysilicon poly-Si silicon) adj liner and contact adj (hole plug) and passivation and liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:25
S31	23	(polysilicon poly-Si silicon) adj liner and contact adj (hole plug) and liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:29
S32	0	silicon adj liner same contact adj (hole plug) same passivation adj (film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:30
S33	4	silicon adj (spacer liner) same contact adj (hole plug) same passivation adj (film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:38
S34	4	silicon adj (spacer liner) same contact adj (hole plug) same passivation adj (film layer) and (spacer liner)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 21:38
S35	0	polysilicon near2 liner and contact adj (hole plug) and passivation adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:02

EAST Search History

S36	2078	polysilicon near2 (layer film liner) and contact adj (hole plug) and passivation adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:03
S37	1324	polysilicon near2 (sidewall side adj wall film liner) and contact adj (hole plug) and passivation adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:03
S38	1265	polysilicon near2 (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:08
S39	1	polysilicon near2 (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj (layer film) and landing adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:04
S40	1047	polysilicon near2 (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:09
S41	999	polysilicon near2 (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj film and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:09
S42	891	polysilicon near1 (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj film and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:09
S43	847	polysilicon adj (sidewall side adj wall film liner) and gate and contact adj (hole plug) and passivation adj film and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:09
S44	133	polysilicon adj (sidewall side adj wall film liner) same contact adj (hole plug) and passivation adj film and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:09
S45	25	polysilicon adj (sidewall side adj wall film liner) same contact adj (hole plug) same passivation adj film and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 14:49

EAST Search History

S46	27	thickness near2 landing adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:10
S47	419	silicon adj nitride near4 gate near6 covered	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:11
S48	4	silicon adj nitride near4 gate near4 covered same passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:20
S49	387	silicon adj nitride near4 gate near4 covered	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:26
S50	46	ILD near2 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:44
S51	17	liner near2 silicon adj nitride same gate same drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:47
S52	0	liner near2 silicon adj nitride same gate same drain same (storage adj node contact adj (plug hole))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:48
S53	6	liner near2 silicon adj nitride same gate same drain and (storage adj node contact adj (plug hole))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 15:48
S54	5	"733984".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 14:13
S55	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2005/12/05 14:13

EAST Search History

S56	1	S55 and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 14:45
S57	2	("5410183").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 14:45
S58	2	("5410183").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/08 21:24
S59	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2006/01/08 21:29
S60	0	("1andinneradjlandingadjpad").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/08 21:29
S61	0	S58 and inner adj landing adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/08 21:29
S62	0	S58 and inner adj landing adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 21:29
S63	1	S59 and inner adj landing adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 21:32
S64	1	S59 and inner adj landing adj pad and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 21:36
S65	1	S59 and inner adj landing adj pad and transistor and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 21:52

EAST Search History

S66	1	S58 and transistor and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 21:52
S67	7	"5410183"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:31
S68	2	("5410183").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:36
S69	6178	passivation adj layer near4 (silicon \$2oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:37
S70	1528	passivation adj layer near1 (silicon \$2oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:37
S71	299	passivation adj layer near1 (silicon \$2oxide).clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:38
S72	222	passivation adj layer near1 (silicon dioxide).clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:40
S73	49	passivation adj layer near1 (silicon adj dioxide).clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 16:40
S74	17279	bit adj line near4 ("via" contact contact adj hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 17:42
S75	1003	bit adj line near4 ("via" contact contact adj hole) and passivati\$2 and ("257"/\$7.ccls. "365"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 17:44

EAST Search History

S76	897	bit adj line near4 (contact contact adj hole) and passivati\$2 and ("257"/\$7.ccls. "365"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 17:44
S77	287	bit adj line near4 (contact adj hole) and passivati\$2 and ("257"/\$7.ccls. "365"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 17:45
S78	93	bit adj line near4 (contact adj hole) and passivati\$2 and ("257"/\$7.ccls. "365"/\$7.ccls. "438"/\$7.ccls.) and interconnect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 17:45
S79	75	bit adj line near4 (contact adj hole) and passivati\$2 and ("257"/\$7.ccls. "365"/\$7.ccls. "438"/\$7.ccls.) and interconnect\$3 and @ad<"20030411"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 18:07
S80	153	landing adj pad near3 (diffusion adj region drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 18:07
S81	53	landing adj pad near3 (diffusion adj region drain source) and memory and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 18:09
S82	4116	barrier near4 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:12
S83	926	barrier near4 (silicon adj nitride) and dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:12
S84	226	barrier near4 (silicon adj nitride) and dram and barrier near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:13
S85	41	barrier near4 (silicon adj nitride) and dram and barrier near4 (lower adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:15

EAST Search History

S86	26	dram and barrier near8 (lower adj electrode) near8 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:32
S87	24	(capacitor dram) and barrier near8 (lower adj electrode) near8 (silicon adj nitride) and ("257"/\$7.ccls. "438"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 18:33
S88	11	"6100138"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 19:11
S89	2	("6100138").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 19:12
S90	1	S89 and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 19:12
S91	971	257/208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 21:07
S92	904	257/211	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 21:07
S93	4809	257/296	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 21:08
S94	6536	((257/208) or (257/211) or (257/296) or (257/301) or (257/304) or (257/311)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 21:08
S95	1	S94 and (landing adj pad).ti,ab,clm. and passivati\$2 adj (layer film).ti, ab,clm. and (contact plug).ti,ab,clm. and (thickness thick).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 21:11

EAST Search History

S98	70	bpsg near2 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/10 16:10
S99	74	bpsg near2 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:10
S10 0	15	bpsg near1 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:22
S10 1	7	bpsg near1 (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:29
S10 2	0	thick near2 nitride near4 capping with BPSG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:30
S10 3	23	nitride with capping with BPSG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:36
S10 4	5	capping adj layer with protect\$3 with BPSG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:37
S10 5	88	capping adj layer with (BSG BPSG)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:42
S10 6	13	capping adj layer with (BSG BPSG) with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:58
S10 7	96	hard adj mask near2 (BSG BPSG)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:58

EAST Search History

S10 8	38	hard adj mask near1 (BSG BPSG)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:58
S10 9	14	hard adj mask near1 (BSG BPSG) with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 0	1010	257/208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 1	944	257/211	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 2	5069	257/296	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 3	2205	257/301	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 4	873	257/304	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 5	643	257/311	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 6	202	257/906	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38
S11 7	233	257/908	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:38

EAST Search History

S11 8	8421	S110 S111 S112 S113 S114 S115 S116 S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:39
S11 9	4	S118 and landing adj pad.clm. and (mao.in. chen.in. nanya.as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:45
S12 0	1	S118 and (bitline bit adj line).ti,ab, clm. and contact.ti,ab,clm. and passivati\$2.ti,ab,clm. and hard adj mask.ti,ab,clm. and landing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:43
S12 1	1	S118 and (bitline bit adj line).ti,ab, clm. and contact.ti,ab,clm. and passivati\$2.ti,ab,clm. and hard adj mask.ti,ab,clm. and (pad landing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:45
S12 2	299	S118 and (mao.in. chen.in. nanya. as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:45
S12 3	148	S118 and (mao.in. chen.in. nanya. as.) and memory.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 17:45
S12 4	11	"6100138"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 07:59
S12 5	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2006/12/19 07:58
S12 6	2	("6100138").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 08:47
S12 7	2	(mao.in. chen.in. nanya.as.) and passivation.clm. and landing adj pad.clm. and transistor.clm. and interconnect\$3.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/19 09:04

EAST Search History

S12 8	6	"083782".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/19 09:13
S12 9	10	((("5966600") or ("6306775") or ("6117725") or ("20020153548") or ("6251726")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 09:13
S13 0	10	(US-20020153548-\$).did. or (US-6251726-\$ or US-6306775-\$ or US-5966600-\$ or US-6117725-\$). did. or (US-20020153548-\$ or US-6306775-\$ or US-6251726-\$ or US-6117725-\$ or US-5966600-\$). did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2006/12/19 09:16
S13 1	1	S130 and landing adj pad	US-PGPUB; USPAT; DERWENT	OR	OFF	2006/12/19 09:19
S13 2	2	("6271073").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 09:19
S13 3	13	(mao.in. chen.in. nayna.as.) and landing adj pad.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/19 10:40
S13 4	7202	((257/208) or (257/211) or (257/296) or (257/301) or (257/304) or (257/311) or (257/906) or (257/908)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 10:40
S13 5	3	S134 and landing adj pad and passivation and transistor and contact and conformal\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/19 10:41
S13 6	0	"5966600".pn. and passivati\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:20
S13 7	2	"5966600".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:25

EAST Search History

S13 8	2	"6100138".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:25
S13 9	2	("5966600").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/13 12:05
S14 0	13	"6174764"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/13 12:05
S14 1	4	((("6174764") or ("6271073"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/13 12:14
S14 2	2	("6100138").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/13 12:57
S14 3	426	contact adj hole near8 (bit adj line bit\$1line) and passivati\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 12:59
S14 4	356	contact adj hole near8 (bit adj line bit\$1line) and passivati\$2 and @ad<"20031212"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 14:09
S14 5	265	passivation adj layer near4 BPSG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 15:07
S14 6	13	passivation adj layer near4 BPSG and bitline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 14:13
S14 7	2	jp-04056324\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 14:13

EAST Search History

S14 8	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2007/05/13 14:32
S14 9	1	(US-20040201043-\$).did. and diffusion	US-PGPUB	OR	OFF	2007/05/13 14:32
S15 0	9688	((257/208) or (257/211) or (257/296) or (257/300) or (257/301) or (257/304) or (257/311) or (257/532) or (257/906) or (257/908)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/13 15:08
S15 1	123	S150 and (storage adj node landing adj pad contact adj pad) and (bit\$1line bit adj line) and passivati\$2 and (transistor MOS MOSFET MISFET FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 15:28
S15 2	7	((mao near1 hui-min).in. (yi-nan near1 chen).in. nanya.as.) and (storage adj node landing adj pad contact adj pad) and (bit\$1line bit adj line) and passivati\$2 and (transistor MOS MOSFET MISFET FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/13 15:29
S15 3	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2007/09/13 18:19
S15 4	2	("5966600").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/13 18:19

EAST Search History

S15 5	220	(US-20040201043-\$ or US-20020135072-\$ or US-20050026329-\$ or US-20040262657-\$ or US-20040206994-\$ or US-20040198007-\$ or US-20040036177-\$ or US-20040000717-\$ or US-20020125508-\$ or US-20020098654-\$ or US-20040262671-\$ or US-20040108535-\$ or US-20040036097-\$ or US-20030027395-\$ or US-20020119624-\$ or US-20050012128-\$ or US-20050095857-\$ or US-20040206996-\$ or US-20050082586-\$ or US-20040201053-\$ or US-20020153548-\$ or US-20040209429-\$ or US-20020109179-\$ or US-20030193827-\$ or US-20050164491-\$ or US-20040021473-\$).did. or (US-20060017085-\$ or US-20050285148-\$ or US-20050199931-\$ or US-20050173747-\$ or US-20050167719-\$ or US-20050124110-\$ or US-20050110066-\$ or US-20050093025-\$ or US-20050090064-\$ or US-20050082590-\$ or US-20050067646-\$ or US-20050062089-\$ or US-20050045936-\$ or US-20050001256-\$ or US-20040238869-\$ or US-20040012046-\$ or US-20040007728-\$ or US-20030205747-\$ or US-20030178661-\$ or US-20030030086-\$ or US-20020121658-\$ or US-20020121657-\$ or US-20010028075-\$ or US-20050104109-\$ or US-20040238863-\$ or US-20030042519-\$ or US-20020119621-\$).did. or (US-20050104144-\$).did. or (US-5966600-\$ or US-6057187-\$ or US-6576944-\$ or US-6885542-\$ or US-6838737-\$ or US-6806187-\$ or US-6787839-\$ or US-6740923-\$ or US-6687984-\$ or US-6870210-\$ or	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/09/14 09:05
9/14/07 6:29:13 PM C:\Documents and Settings\monddr\My Documents\EAST\Workspaces\10733984.wsp					Page 19	

EAST Search History

S15 6	160	S155 and BPSG and lining landing adj pad and contact adj plug and polysilicon	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/09/14 09:06
S15 7	20	S155 and BPSG and (lining landing adj pad conformal\$2) and contact adj plug and polysilicon	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/09/14 09:09
S15 8	2	("6271073").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 09:52
S15 9	6	"155593".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 09:52
S16 0	0	S159 and remotely near5 (diagnostic\$1 monitoring directed adj maintenance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 09:54
S16 1	1	S159 and remote\$3 and (diagnostic\$1 monitoring directed adj maintenance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:34
S16 2	311	gate adj cap adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 11:03
S16 3	0	gate adj cap adj layer and passivation adj layer and contact adj plug and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:35
S16 4	1	gate adj cap adj layer and passivation adj layer and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:54
S16 5	32	cap adj layer and passivation adj layer and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:55

EAST Search History

S16 6	1	S164 and cap adj layer and passivation adj layer and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:56
S16 7	7	gate near3 (cap adj layer) and passivation adj layer and contact adj plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 10:56
S16 8	14	gate adj cap adj layer and cap near4 protect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 11:29
S16 9	695	gate adj stack near4 insulati\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 11:29
S17 0	28	gate adj stack near4 insulati\$2 near4 protect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 15:02
S17 2	965	diffusion adj barrier near3 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 11:58
S17 3	5	diffusion adj barrier near2 oxide and contact adj plug and transistor and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 12:00
S17 4	31	diffusion adj barrier near2 oxide.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 12:21
S17 5	15	landing adj pad near6 (thick thickness) and contact adj plug and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 12:52
S17 6	11	silicon adj nitride near4 (landing adj pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 12:52

EAST Search History

S17 7	222	(US-20040201043-\$ or US-20020135072-\$ or US-20050026329-\$ or US-20040262657-\$ or US-20040206994-\$ or US-20040198007-\$ or US-20040036177-\$ or US-20040000717-\$ or US-20020125508-\$ or US-20020098654-\$ or US-20040262671-\$ or US-20040108535-\$ or US-20040036097-\$ or US-20030027395-\$ or US-20020119624-\$ or US-20050012128-\$ or US-20050095857-\$ or US-20040206996-\$ or US-20050082586-\$ or US-20040201053-\$ or US-20020153548-\$ or US-20040209429-\$ or US-20020109179-\$ or US-20030193827-\$ or US-20050164491-\$ or US-20040021473-\$).did. or (US-20060017085-\$ or US-20050285148-\$ or US-20050199931-\$ or US-20050173747-\$ or US-20050167719-\$ or US-20050124110-\$ or US-20050110066-\$ or US-20050093025-\$ or US-20050090064-\$ or US-20050082590-\$ or US-20050067646-\$ or US-20050062089-\$ or US-20050045936-\$ or US-20050001256-\$ or US-20040238869-\$ or US-20040012046-\$ or US-20040007728-\$ or US-20030205747-\$ or US-20030178661-\$ or US-20030030086-\$ or US-20020121658-\$ or US-20020121657-\$ or US-20010028075-\$ or US-20050104109-\$ or US-20040238863-\$ or US-20030042519-\$ or US-20020119621-\$).did. or (US-20050104144-\$).did. or (US-5966600-\$ or US-6057187-\$ or US-6576944-\$ or US-6885542-\$ or US-6838737-\$ or US-6806187-\$ or US-6787839-\$ or US-6740923-\$ or US-6687984-\$ or US-6870710-\$ or	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/09/14 14:04
9/14/07 6:29:13 PM	C:\Documents and Settings\mondm\My Documents\EAST\Workspaces\10733984.wsp				Page 22	

EAST Search History

S17 8	6	S177 and landing adj pad near4 cover\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 14:08
S17 9	102	(semiconductor integrated adj circuit)and landing adj pad near4 cover\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 14:09
S18 0	102	(semiconductor integrated adj circuit) and landing adj pad near4 cover\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 14:12
S18 1	102	(semiconductor integrated adj circuit) and landing adj pad near4 cover\$3 and landing adj pad	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 14:12
S18 2	1	(US-20040201043-\$).did.	US-PGPUB	OR	OFF	2007/09/14 14:40
S18 3	1	(US-20040201043-\$).did. and silicon adj nitride	US-PGPUB	OR	ON	2007/09/14 14:40
S18 4	11	landing adj pad near4 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 15:12
S18 5	45	landing adj pad near8 (silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/14 16:26
S18 6	2	("6548394").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/14 15:17